

N-Channel 100 V MOSFET

Product summary

V_{DS} (V)	$R_{DS(on), Typ}$ (m Ω)	I_D (A)
100	1.0 @ $V_{GS} = 10V$	400 ⁽¹⁾

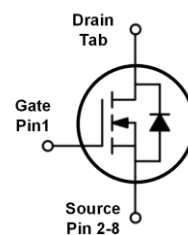
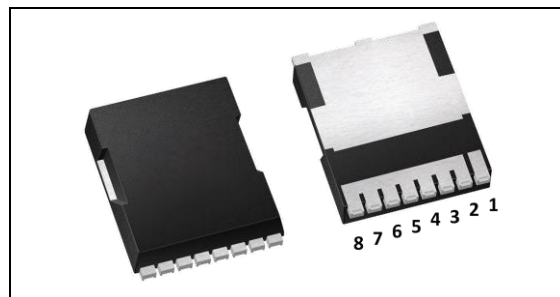
Features

- Low $R_{DS(on)}$ SGT technology
- Low thermal impedance
- Fast switching speed
- 100% avalanche tested

Applications

- DC/DC conversion
- Power switch
- Motor drives

TOLL



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HALOGEN
FREE

1. Maximum ratings

Absolute maximum ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source voltage		V_{DS}	100	V
Gate-source voltage		V_{GS}	± 20	
Continuous drain current	$T_C = 25^\circ\text{C}$ ⁽¹⁾	I_D	400	A
	$T_C = 100^\circ\text{C}$		280	
	$T_A = 25^\circ\text{C}$ ⁽⁴⁾		33	
Pulsed drain current ⁽²⁾		$I_{D,pulse}$	1320	
Avalanche energy, single pulse ⁽³⁾		E_{AS}	540	mJ
Power dissipation	$T_C = 25^\circ\text{C}$	P_D	431	W
	$T_A = 25^\circ\text{C}$ ⁽⁴⁾		3.1	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

2. Thermal resistance ratings

Thermal resistance ratings						
Parameter		Symbol	Max.	Unit		
Thermal resistance, junction-to-case	Steady state	$R_{\theta JC}$	0.29	°C/W		
Thermal resistance, junction-to-ambient ⁽⁴⁾	Steady state	$R_{\theta JA}$	40			

3. Electrical characteristics

Electrical characteristics (T _J = 25°C unless otherwise noted)						
Parameter	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Static parameter						
Drain to source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 1 mA	100			V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2.0	3.0	4.0	V
Gate-body leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V			1	μA
Drain-source on-resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 100 A		1.0	1.2	mΩ
Forward transconductance ⁽⁵⁾	g _{fs}	V _{DS} = 5 V, I _D = 100 A		260		S
Gate resistance	R _g	f = 1 MHz		4.0		Ω
Dynamic ⁽⁵⁾						
Total gate charge	Q _g	V _{DS} = 50 V, I _D = 100 A, V _{GS} = 10 V		260		nC
Gate-source charge	Q _{gs}			75		
Gate-drain charge	Q _{gd}			76		
Turn-on delay time	t _{d(on)}	V _{DS} = 50 V, I _D = 100 A, V _{GS} = 10 V, R _{GEN} = 6 Ω		81		ns
Rise time	t _r			178		
Turn-off delay time	t _{d(off)}			167		
Fall time	t _f			68		
Input capacitance	C _{iss}	V _{DS} = 50 V, V _{GS} = 0 V, f = 1 MHz		14000		pF
Output capacitance	C _{oss}			5300		
Reverse transfer capacitance	C _{rss}			353		
Reverse Diode Characteristics ⁽⁵⁾						
Diode forward voltage	V _{SD}	V _{GS} = 0 V, I _F = 100 A		0.85	1.1	V
Reverse recovery time	t _{rr}	V _{DS} = 50 V, I _F = 100 A, di/dt = 100 A/μs		92		ns
Reverse recovery charge	Q _{rr}			200		nC

Notes

- (1) Package limited.
- (2) Pulse width limited by maximum junction temperature.
- (3) $V_{DS} = 75\text{ V}, V_{GS} = 10\text{ V}, L = 0.3\text{ mH}$.
- (4) $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5x1.5 in. board of FR-4 material.
- (5) Guaranteed by design, not subject to production testing.

4. Electrical characteristics diagrams

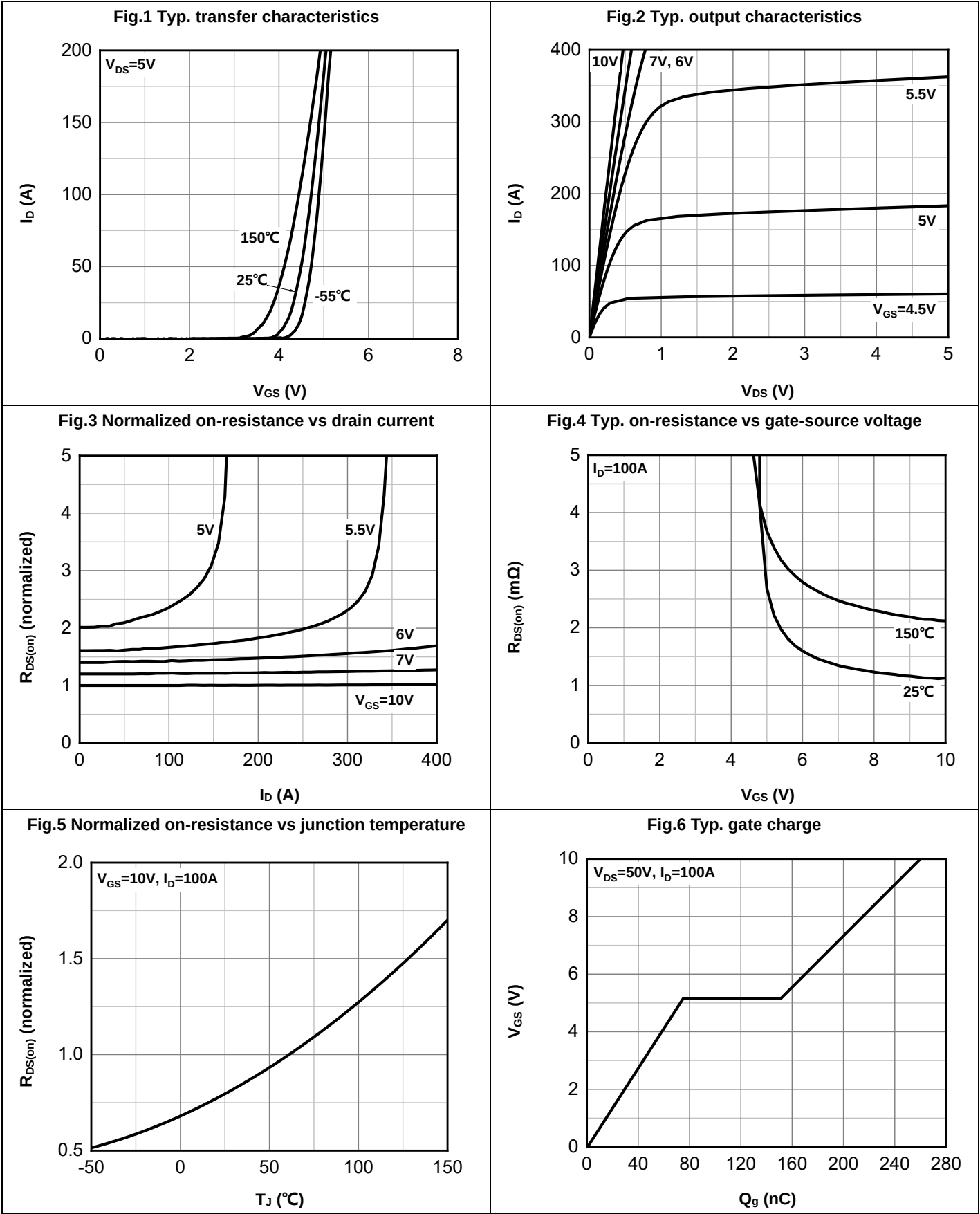


Fig.7 Typ. forward characteristics of body diode

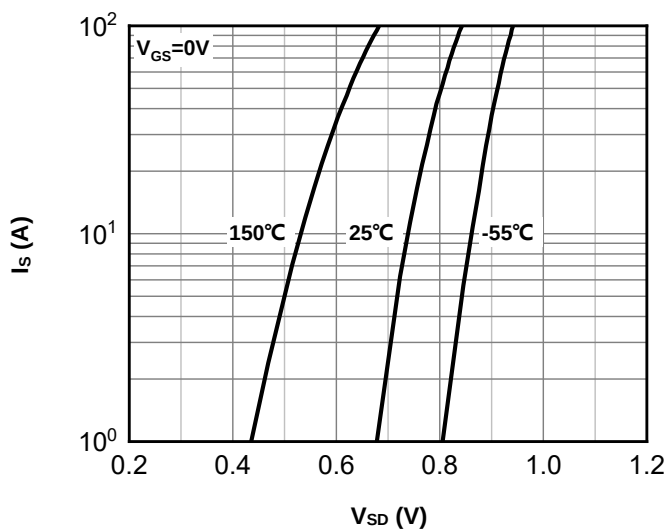


Fig.8 Safe operating area

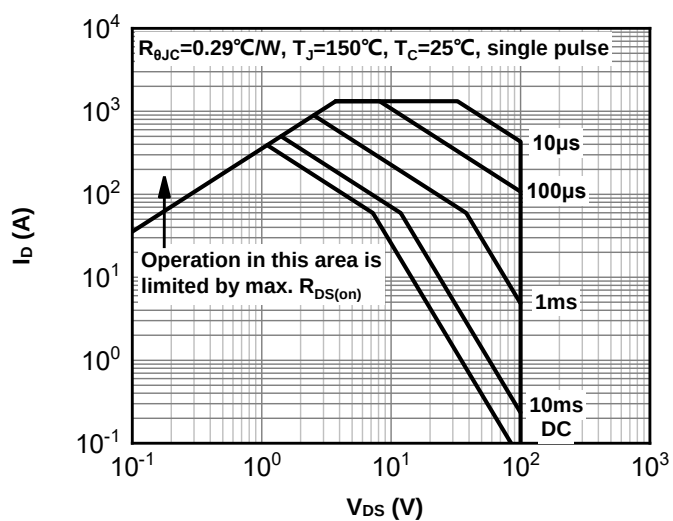


Fig.9 Typ. Capacitance

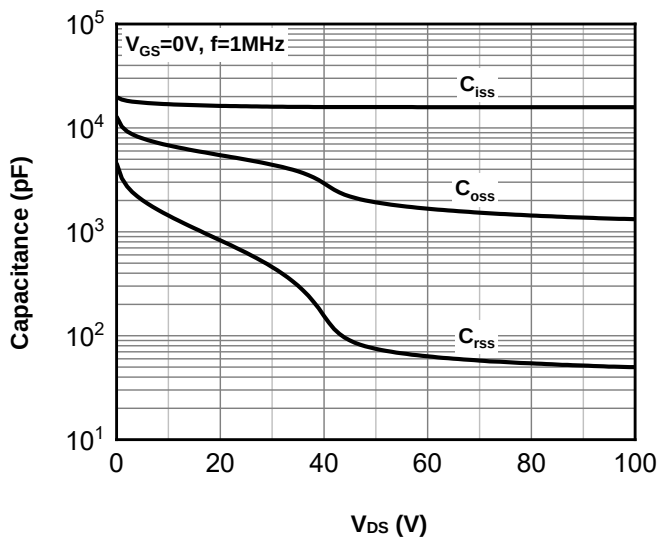


Fig.10 Single pulse maximum power dissipation

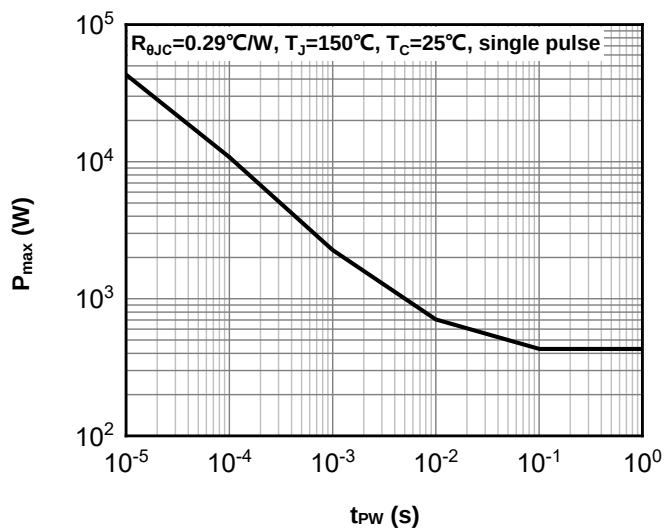


Fig.11 Max. power dissipation vs case temperature

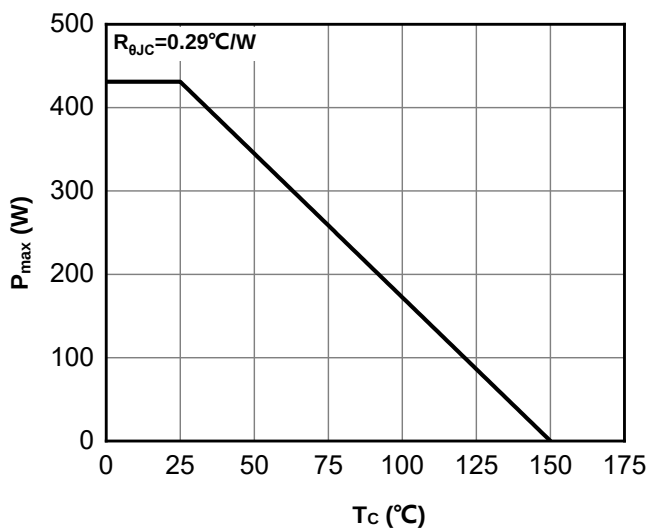
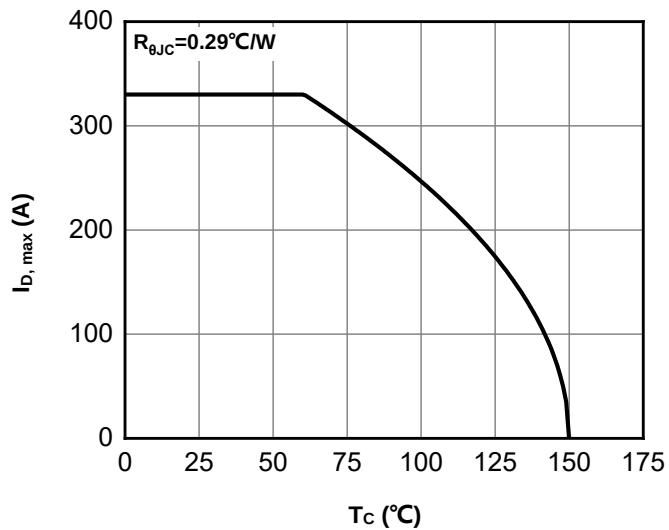
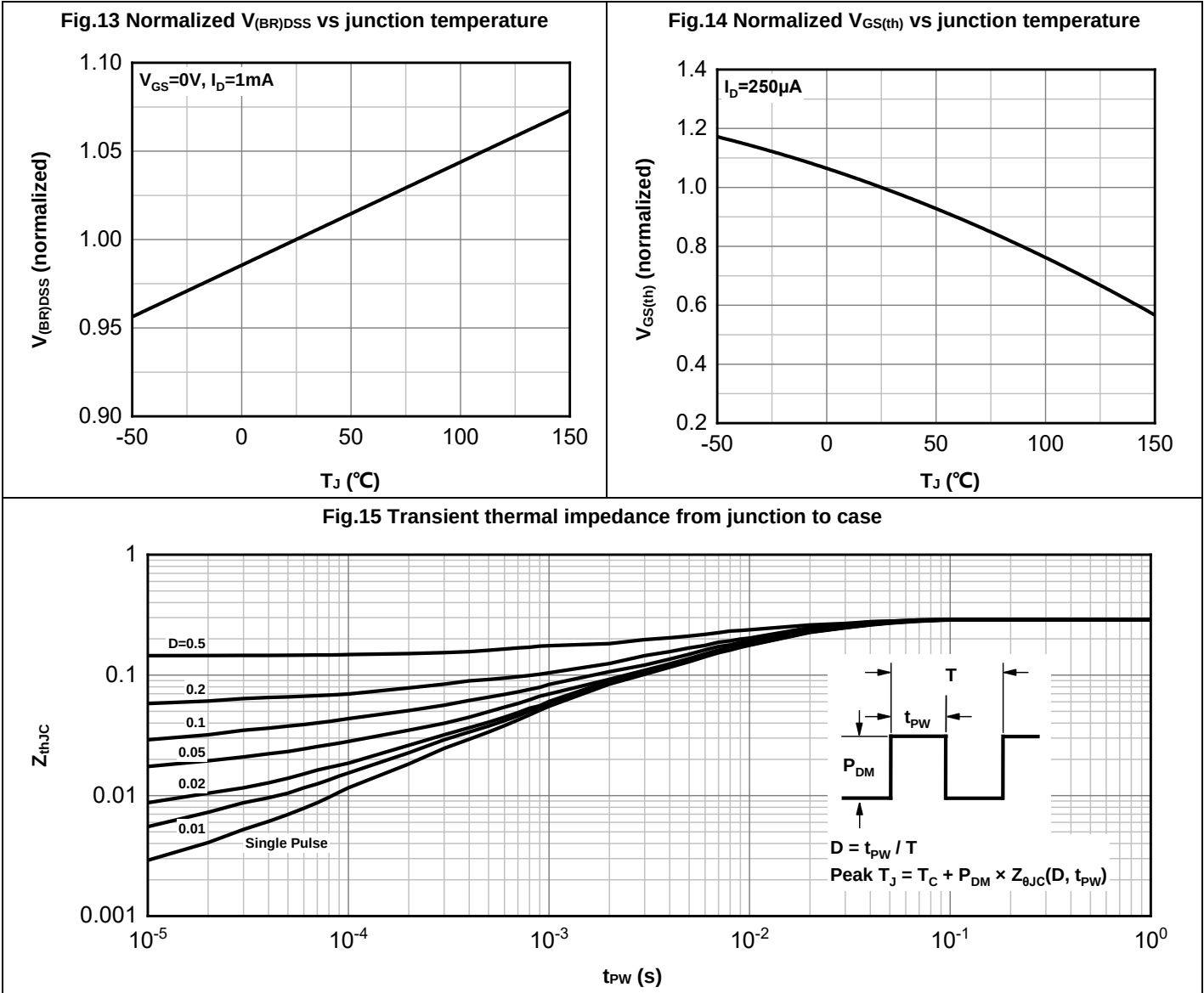
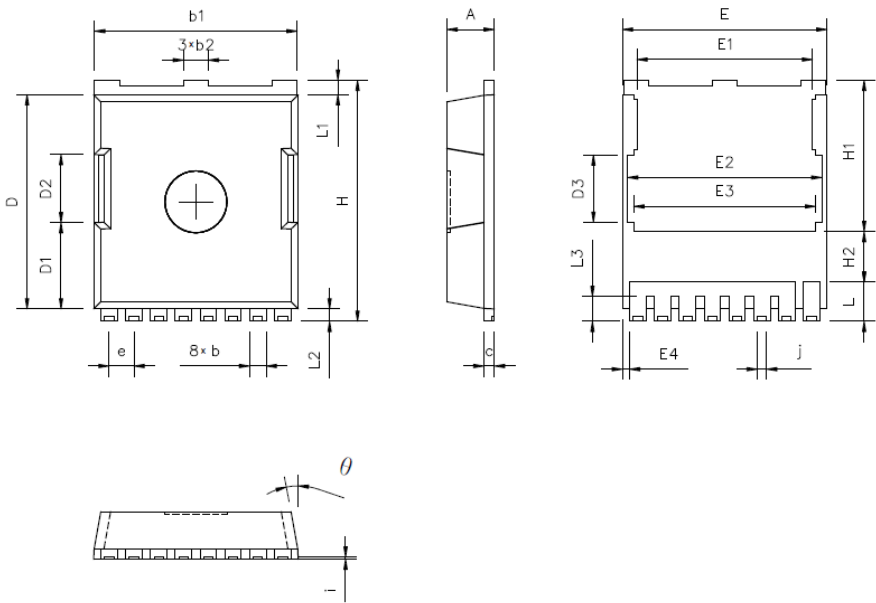


Fig.12 Max. continuous drain current vs case temperature





5. Package outline dimensions



Dim	Millimeters		
	Min	Nom	Max
A	2.20	-	2.40
b	0.70	-	0.90
b1	9.70	-	9.90
b2	1.20 REF		
c	0.40	-	0.60
D	10.28	-	10.48
D1	4.08	-	4.28
D2	3.20	-	3.40
D3	3.16	-	3.36
E	9.80	-	10.00
E1	8.40	-	8.60
E2	9.30	-	9.50
E3	8.80 REF		
E4	0.25	-	0.45
e	1.20 BASIC		
H	11.58	-	11.78
H1	7.23	-	7.43
H2	2.45 REF		
i	0.10	-	-
j	0.45 REF		
L	1.60	-	2.10
L1	0.60	-	0.80
L2	0.50	-	0.70
L3	1.05	-	1.30
θ	10° REF		